

NSS1C200MZ4

100 V, 2.0 A, Low $V_{CE(sat)}$ PNP Transistor

ON Semiconductor's e²PowerEdge family of low $V_{CE(sat)}$ transistors are miniature surface mount devices featuring ultra low saturation voltage ($V_{CE(sat)}$) and high current gain capability. These are designed for use in low voltage, high speed switching applications where affordable efficient energy control is important.

Typical applications are DC-DC converters and power management in portable and battery powered products such as cellular and cordless phones, PDAs, computers, printers, digital cameras and MP3 players. Other applications are low voltage motor controls in mass storage products such as disc drives and tape drives. In the automotive industry they can be used in air bag deployment and in the instrument cluster. The high current gain allows e²PowerEdge devices to be driven directly from PMU's control outputs, and the Linear Gain (Beta) makes them ideal components in analog amplifiers.

- This is a Pb-Free Device

MAXIMUM RATINGS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Max	Unit
Collector-Emitter Voltage	V_{CEO}	-100	Vdc
Collector-Base Voltage	V_{CB}	-140	Vdc
Emitter-Base Voltage	V_{EB}	-7.0	Vdc
Base Current - Continuous	I_B	1.0	Adc
Collector Current - Continuous - Peak	I_C	2.0 3.0	Adc
Total Power Dissipation Total P_D @ $T_A = 25^\circ\text{C}$ (Note 1) Total P_D @ $T_A = 25^\circ\text{C}$ (Note 2)	P_D	2.0 0.8	W
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient (Note 1) Junction-to-Ambient (Note 2)	$R_{\theta JA}$	64 155	$^\circ\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes, 1/8" from case for 5 seconds	T_L	260	$^\circ\text{C}$

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

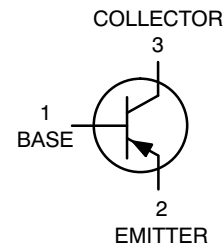
1. mounted on 1" sq. (645 sq. mm) Collector pad on FR-4 bd material
2. mounted on 0.012" sq. (7.6 sq. mm) Collector pad on FR-4 bd material



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-100 VOLTS, 2.0 AMPS PNP LOW $V_{CE(sat)}$ TRANSISTOR

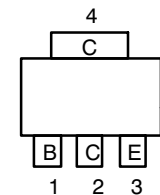


MARKING DIAGRAM



- A = Assembly Location
- Y = Year
- W = Work Week
- 1C200 = Specific Device Code
- = Pb-Free Package

PIN ASSIGNMENT



Top View Pinout

ORDERING INFORMATION

Device	Package	Shipping†
NSS1C200T1G	SOT-223 (Pb-Free)	1000/ Tape & Reel
NSS1C200T3G	SOT-223 (Pb-Free)	4000/ Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specification Brochure, BRD8011/D.

NSS1C200MZ4

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector-Emitter Breakdown Voltage (I _C = -10 mAdc, I _B = 0)	V _{(BR)CEO}	-100			Vdc
Collector-Base Breakdown Voltage (I _C = -0.1 mAdc, I _E = 0)	V _{(BR)CBO}	-140			Vdc
Emitter-Base Breakdown Voltage (I _E = -0.1 mAdc, I _C = 0)	V _{(BR)EBO}	-7.0			Vdc
Collector Cutoff Current (V _{CB} = -140 Vdc, I _E = 0)	I _{CBO}			-100	nAdc
Emitter Cutoff Current (V _{EB} = -6.0 Vdc)	I _{EBO}			-50	nAdc

ON CHARACTERISTICS

DC Current Gain (Note 3) (I _C = -10 mA, V _{CE} = -2.0 V) (I _C = -500 mA, V _{CE} = -2.0 V) (I _C = -1.0 A, V _{CE} = -2.0 V) (I _C = -2.0 A, V _{CE} = -2.0 V)	h _{FE}	150 120 80 50		360	
Collector-Emitter Saturation Voltage (Note 3) (I _C = -0.1 A, I _B = -0.010 A) (I _C = -0.5 A, I _B = -0.050 A) (I _C = -1.0 A, I _B = -0.100 A) (I _C = -2.0 A, I _B = -0.200 A)	V _{CE(sat)}			-0.040 -0.080 -0.125 -0.220	V
Base-Emitter Saturation Voltage (Note 3) (I _C = -1.0 A, I _B = -0.100 A)	V _{BE(sat)}			-0.950	V
Base-Emitter Turn-on Voltage (Note 3) (I _C = -1.0 A, V _{CE} = -2.0 V)	V _{BE(on)}			-0.850	V
Cutoff Frequency (I _C = -100 mA, V _{CE} = -5.0 V, f = 100 MHz)	f _T		120		MHz
Input Capacitance (V _{EB} = 3.0 V, f = 1.0 MHz)	C _{ibo}		200		pF
Output Capacitance (V _{CB} = 10 V, f = 1.0 MHz)	C _{obo}		22		pF

3. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

TYPICAL CHARACTERISTICS

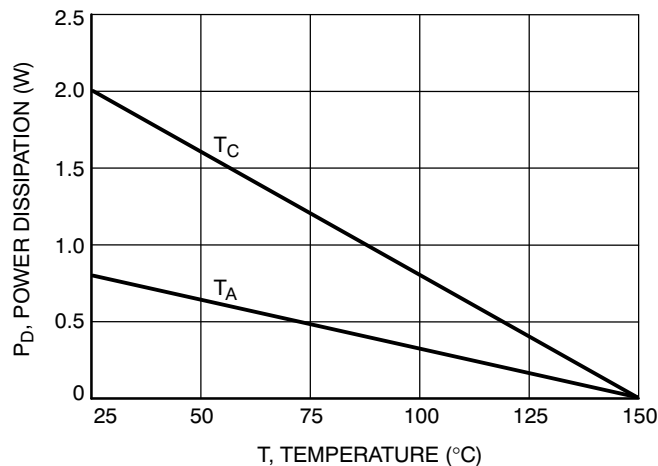


Figure 1. Power Derating

TYPICAL CHARACTERISTICS

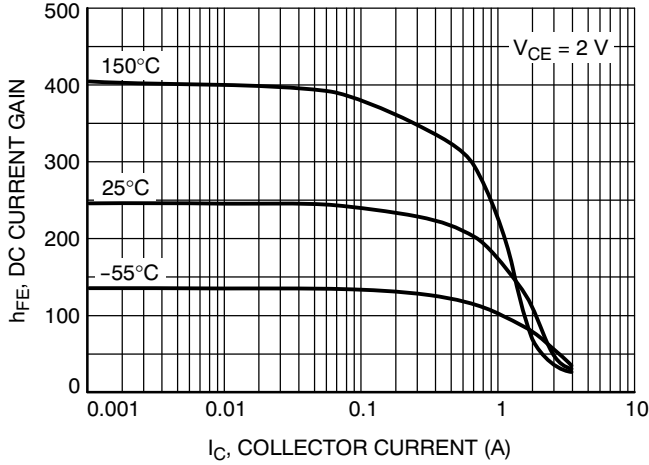


Figure 2. DC Current Gain

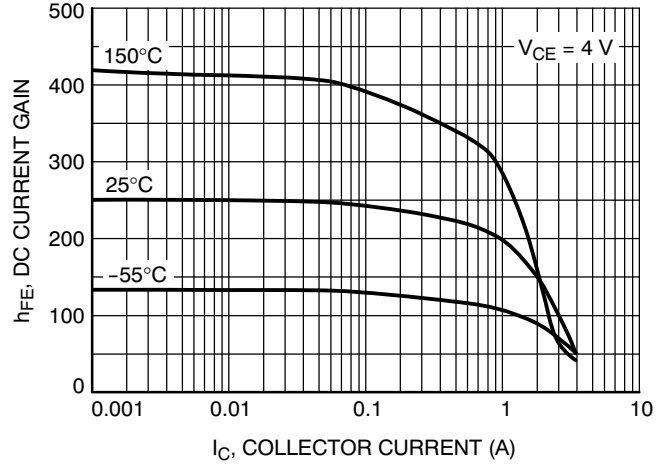


Figure 3. DC Current Gain

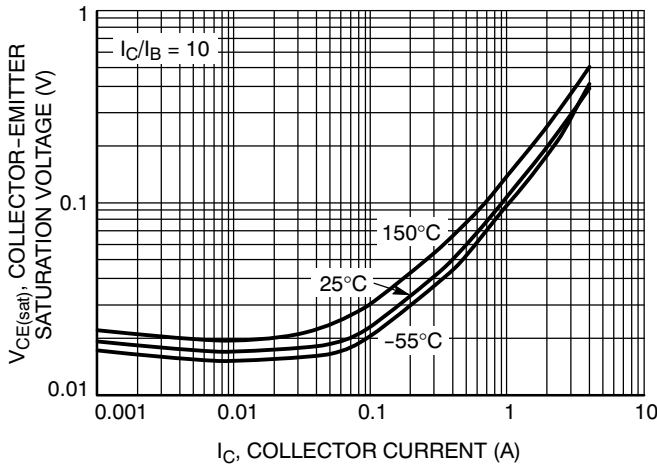


Figure 4. Collector-Emitter Saturation Voltage

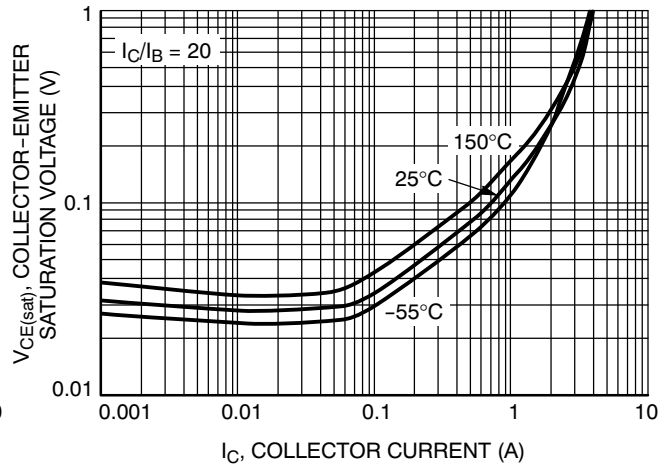


Figure 5. Collector-Emitter Saturation Voltage

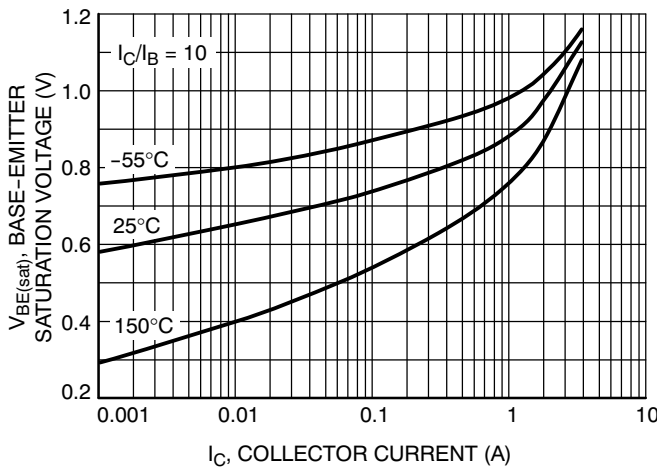


Figure 6. Base-Emitter Saturation Voltage

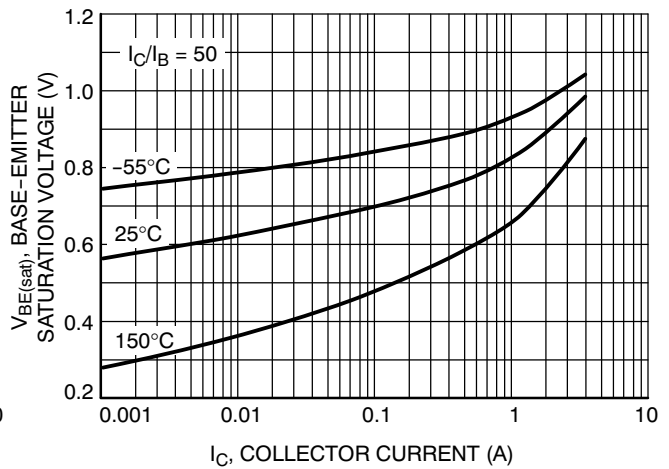


Figure 7. Base-Emitter Saturation Voltage

NSS1C200MZ4

TYPICAL CHARACTERISTICS

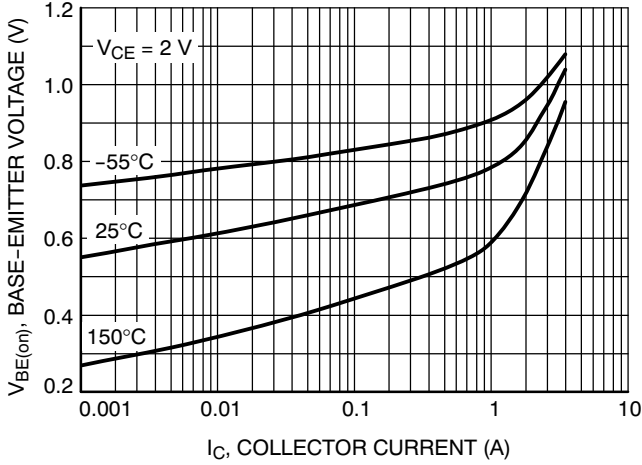


Figure 8. Base-Emitter Voltage

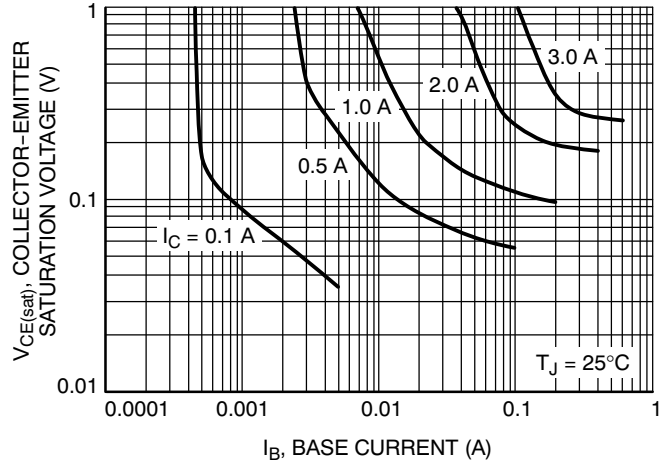


Figure 9. Collector Saturation Region

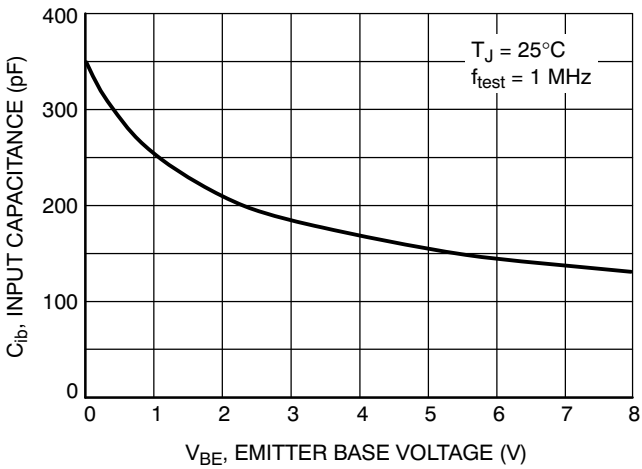


Figure 10. Input Capacitance

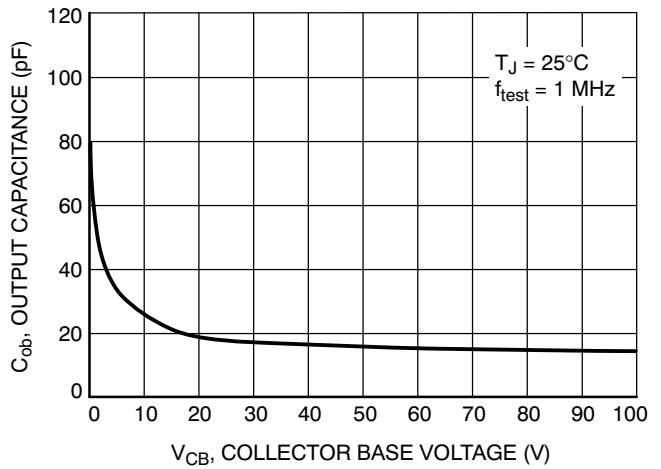


Figure 11. Output Capacitance

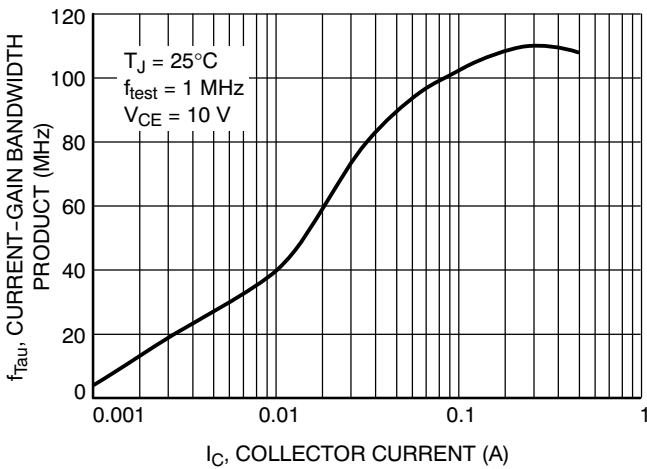


Figure 12. Current-Gain Bandwidth Product

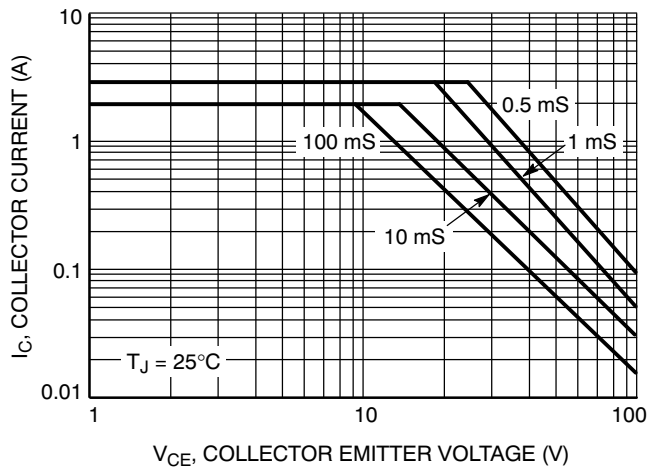
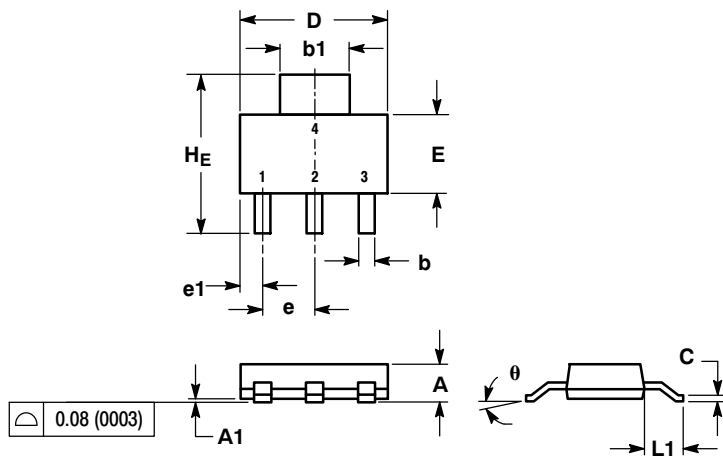


Figure 13. Safe Operating Area

NSS1C200MZ4

PACKAGE DIMENSIONS

SOT-223 (TO-261)
CASE 318E-04
ISSUE L



NOTES:

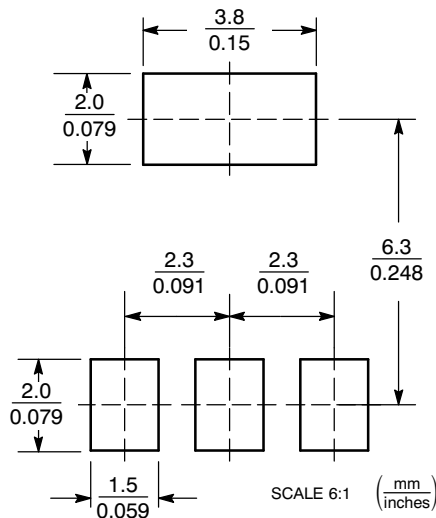
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L1	1.50	1.75	2.00	0.060	0.069	0.078
HE	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	-	10°	0°	-	10°

STYLE 1:

- PIN 1. BASE
- COLLECTOR
- EMITTER
- COLLECTOR

SOLDERING FOOTPRINT



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